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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Application Number	10/028001
Filing Date	20, 2002
First Named Inventor	Forbes, Leonard
Group Art Unit	2818
Examiner Name	Unknown

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Attorney Docket No: 01303.035US1

US PATENT DOCUMENTS

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
	US-4412902	11/01/1983	Michikami, Osamu et al	204	192	06/18/1982
TH	US-4780424	10/25/1988	Holler, Mark A	437	29	09/28/1987
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Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T ²
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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
TH		AFANAS'EV, V., et al. "Electron energy barriers between (100)Si and ultrathin stacks of SiO ₂ , Al ₂ O ₃ , and ZrO ₃ and ZrO ₂ insulators", <u>Applied Physics Letters</u> , 78(20), (2001),pp. 3073-3075	
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		Transactions of the Metallurgical Society of AIME, 233, (1965), pp. 497-501	
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Note: MONTH and/or YEAR when not specified are unknown. TH

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Substitute Disclosure Statement Form (PTO-1449)

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